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26. (AMENDED) Apparatus for lining a semiconductor processing chamber comprising:

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- a liner having a plurality of apertures formed at least partially therein;
- a lid having an inlet, the lid disposed proximate the liner and defining a plenum at least partially therebetween; and
- a nozzle disposed in at least one of apertures.

Please added the following claims:

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--37. (NEW) The apparatus of claim 25, wherein the second side of the liner is textured.

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38. (NEW) Apparatus for lining a process volume defined by sidewalls of a semiconductor processing chamber comprising:

- a liner adapted to be removably disposed in the process volume; and
- a passage at least partially formed in the liner isolated from the process volume and adapted to flow a heat transfer medium therethrough.

39. (NEW) The apparatus of claim 38, wherein the liner further comprises:
a cylindrical wall.

40. (NEW) The apparatus of claim 39, wherein the passage is formed at least partially in the cylindrical wall.

41. (NEW) The apparatus of claim 39, wherein the liner further comprises:
a bottom coupled to the cylindrical wall.

42. (NEW) The apparatus of claim 41, wherein the passage is formed at least partially in the bottom.

43. (NEW) The apparatus of claim 39, wherein the cylindrical wall is configured to line the sidewalls to the chamber.

44. (NEW) The apparatus of claim 39, wherein the cylindrical wall is configured to line a substrate support disposed in the process volume of the chamber.

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45. (NEW) The apparatus of claim 38, wher in the liner further comprises:
an outer cylindrical wall;
an inner cylindrical wall; and
a bottom coupled between the outer cylindrical wall and the inner cylindrical wall.

46. (NEW) The apparatus of claim 45, wherein the passage is formed in at least partially in at least one of the inner cylindrical wall, outer cylindrical wall and the bottom.

47. (NEW) A semiconductor processing chamber comprising:
a wall, a bottom and a lid assembly defining a chamber volume;
a substrate support disposed within the chamber volume; and,
a chamber liner having at least a first portion disposed proximate the wall, the chamber liner having a passage fluidly isolated from the chamber volume at least partially formed in the chamber liner.

48. (NEW) The chamber of claim 47, wherein the chamber liner further comprises:

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a second portion disposed proximate the lid assembly.

49. (NEW) The chamber of claim 48, wherein the second portion of the chamber liner further comprises:

a plurality of apertures formed therethrough.

50. (NEW) The chamber of claim 49 further comprising a plate disposed on the chamber liner and forming a plenum therewith, the plenum in fluid communication with the chamber volume through the apertures.

51. (NEW) A semiconductor processing chamber comprising:

a wall, a bottom and a lid assembly defining a chamber volume;

a substrate support disposed within the chamber volume; and,